



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Jun Ito, et al.

Serial No.: 10/020,460

Group Art Unit: 2811

Filed: December 18, 2001

Examiner: S. Crane

For: GROUP III NITRIDE COMPOUND SEMICONDUCTOR DEVICE

Honorable Commissioner of Patents
Washington, D.C. 20231

AMENDMENT UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated January 29, 2003, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims to read as follows:

1. (Amended) A semiconductor device comprising:
a substrate;
an undercoat layer formed on said substrate and comprising a metal nitride; and
a group III nitride compound semiconductor layer formed on said undercoat layer, and
separated from said substrate by at least said undercoat layer.
2. (Amended) A semiconductor device according to claim 1, wherein said metal nitride directly contacts said group III nitride compound semiconductor layer.
4. (Amended) A semiconductor device according to claim 1, wherein said undercoat layer comprises at least one member selected from the group consisting of titanium nitride, zirconium nitride, hafnium nitride, tantalum nitride, and a nitride of a metal alloy.
5. (Amended) A semiconductor device according to claim 1, wherein said substrate comprises one member selected from the group consisting of sapphire, silicon carbide, gallium nitride, silicon, gallium phosphide, and gallium arsenide.

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Amend B
Y Redine
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